



Multimedia Available: Applied Materials Introduces Critical Epi Technology for Advanced Transistor Designs

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Jul 14, 2003 (BUSINESS WIRE) -- Applied Materials Inc. introduces its 300mm Epi RP Centura(R) system, the industry's only system to deliver facet-free 100 percent selective epitaxial deposition and consistent greater than 1E20 atoms/cm(3) activated dopant incorporation for all sub-90nm applications, including source/drain (S/D) extensions, raised S/D and other emerging transistor designs. The Epi RP also provides high productivity, low cost of operation and greater than 2x the throughput of competitive systems.

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